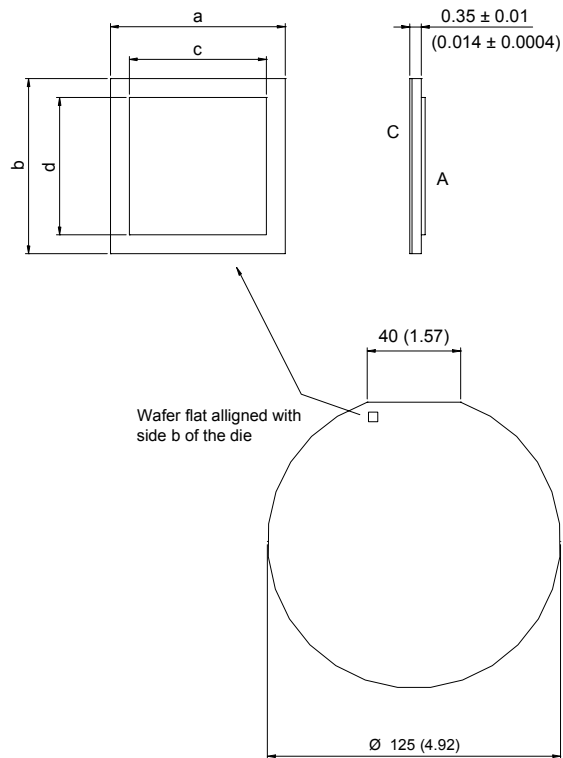


Fred Die in Wafer Form



NOTES:

1. ALL DIMENSIONS ARE SHOWN IN MILLIMETERS (INCHES).
2. CONTROLLING DIMENSION (INCH):
3. DIMENSIONS AND TOLERANCES:
 $a = 5.080 \pm 0.05$
(0.200 ± 0.002)
 $b = 5.08 \pm 0.05$
(0.200 ± 0.002)
 $c = 4.420 \pm 0.003$
(0.174 ± 0.0001)
 $d = 4.420 \pm 0.003$
(0.174 ± 0.0001)
4. LETTER DESIGNATION:
A = Anode (Top Metal)
C = Cathode (Back Metal)
5. SAWING:
Recommended Blade
SEMITEC S1025 QS00 Blade
6. MINIMUM ORDER QUANTITY:
300 die

NOT TO SCALE

Electrical Characteristics (Wafer Form)

Parameters	Units	Test Conditions
V _{FM} Maximum Forward Voltage	2.3 V	T _J = 25°C, I _F = 30 A
V _{RRM} Minimum Reverse Breakdown Voltage	600 V	T _J = 25°C, I _{RRM} = 200 μA
I _{RM} Max. Reverse Leakage Current	100 μA	T _J = 25°C, V _{RRM} = 600 V
t _{rr} Typ. Reverse Recovery Time	20 ns	I _F = 1 A, di/dt = 100 A/μs, V _R = 30 V

Mechanical Data

Nominal Back Metal Composition, Thickness	Cr - Ni - Ag (1 KA - 2 KA - 3 KA)
Nominal Front Metal Composition, Thickness	99% Al, 1% Si (3 microns)
Chip Dimensions	0.200" x 0.200" (see drawing)
Reject Ink Dot Size	0.25 mm diameter minimum
Recommended Storage Environment	Storage in original container, in dessicated nitrogen, with no contamination

Ordering Information Table

Device Code	
1 - Fred Die	
2 - Chip Dimension in Mils:	200 = 200x200 square
3 - Process	H = HyperFast
4 - Voltage code Vrrm (*100) eg:	06 = 600V
5 - Chip surface metallization:	A = Aluminium (anode), Silver (cathode)
6 - Wafer diameter in inches	
7 - Packaging:	B = Inked Probed Unsaun Wafer (Wafer in box)